Tunneling magnetoresistance phenomenon utilizing graphene magnet electrode

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Using magnetic rare-metals for spintronic devices is facing serious problems for the environmental contamination and the limited material-resource. In contrast, by fabricating ferromagnetic graphene nanopore arrays (FGNPAs) consisting of honeycomb-like array of hexagonal nanopores with hydrogen-terminated zigzag-type atomic structure edges, we reported observation of polarized electron spins spontaneously driven from the pore edge states, resulting in rare-metal-free flat-energy-band ferromagnetism. Here, we demonstrate observation of tunneling magnetoresistance (TMR) behaviors on the junction of cobalt/SiO2/FGNPA electrode, serving as a prototype structure for future rare-metal free TMR devices using magnetic graphene electrodes. Gradual change in TMR ratios is observed across zero-magnetic field, arising from specified alignment between pore-edge and cobalt-spins. The TMR ratios can be controlled by applying back-gate voltage and by modulating inter pore distance. Annealing the SiO2/FGNPA junction also drastically enhances TMR ratios up to ~100%. © 2014 AIP Publishing LLC. [http://dx.doi.org/10.1063/1.4901279]

Several key components of spintronics have been realized in recent years, e.g., giant magnetoresistance (GMR), tunneling MR (TMR), and spin valve devices.1–3 Giant TMR ratios, (RAP − RP)/RP, where AP and P refer to antiparallel and parallel orientations of the spin configurations of the two electrodes, of ~100% have been obtained in CoFeB/MgO/CoFeB junctions. A wide variety of materials have been utilized for spintronic devices such as ferromagnetic metals and1–3 ferromagnetic semiconductors.4–6 In all cases, however, rare magnetic elements are essential to provide polarized spins to the systems.

In contrast, it was theoretically predicted that graphene edges with specified atomic structures (the so-called zigzag edge, Fig. 1(b)) are spontaneously spin polarized, exhibiting flat-energy-band ferromagnetism caused from extremely high electronic density of spin states (i.e., the edge states) and a strong spin interaction among the localized electrons.7–9 Importantly, this occurs despite the absence of rare magnetic elements, considering just carbon atoms with sp2 orbitals. In the case of graphene nanoribbons (GNR, Fig. 1(b)),10 the appearance of the spin polarization is highly sensitive to the spin interaction between the two edges and is determined so as to maximize exchange energy gain (similar to Hund’s rule in atoms). In particular, spin ground states in GNRs under absent magnetic fields are still under debating stages. These properties suggest that novel types of spin-based devices may be realized using graphene-based materials, without the need of rare magnetic atoms. Long spin diffusion lengths and the introduction of the spin-orbit interaction by hydrogenation11,12 are further recent examples of the potential of graphene spintronics.

In prior works, we have experimentally confirmed the formation of this flat-band ferromagnetism in hydrogen (H)-terminated zigzag-edged GNPAs (Figs. 1(a) and 1(b)).13–16 Because the GNPAs corresponds to a large ensemble of the zigzag GNRs (i.e., interpore regions), it is effective to detect small magnetic and electric signals arising from the pore edge spins. Observation of the significant reduction of the G/D peak ratios by the critical-temperature annealing (~800 °C) in Raman spectrum and the comparison with the previous other experiments (e.g., extremely low G/D peak ratios in the intentionally fabricated zigzag-edge hexagonal pores17 and in the zigzag-edged graphene flakes,18 atomic reconstruction to zigzag edge by Joule heating,19 and electron beam irradiation20) implied the formation of the zigzag-type atomic structure of the pore edges by the reconstruction of the edge atomic structure. Moreover, observation of the ferromagnetism induced by decreasing the inter pore distance and of the high density of the polarized spins at the pore edges by magnetic force microscope in the ferromagnetic graphene nanopore arrays (FGNPAs)13,14 suggested that the observed ferromagnetism was attributed to the presence of the polarized spins existing at the pore edges. Two theoretical analysis (GNR theory and Lieb’s theorem21,22) of the observed magnetization values (~0.3 μB/edge dangling bond) also suggested that the mono-hydrogenated zigzag pore edges were the origin for the ferromagnetism.13,15 Recent our work has proved...
magnetization measurement of the layered structure of the SiO$_2$/FGNPA implies the persistence of the ferromagnetic signal even after evaporation of the SiO$_2$ film on the pore edges, although the magnitude is reduced somewhat compared with that without SiO$_2$ film.

Figures 2(a) and 2(b) give the result of a typical TMR measurement of the Co/SiO$_2$/FGNPA junction (shown in Figs. 1(c) and 1(d)) under in-plane parallel $B$ at (a) 1.5 K and (b) 300 K. We identify the minimum resistance ($R_{\text{min}}$) as the situation in which the external $B$ induces best matching between the spin polarizations of the magnetic materials (i.e., parallel spin alignment between cobalt and FGNPA) and take this as $R_P$ in subsequent calculations of TMR ratios, as mentioned in the figure caption. The observed TMR behaviors in Fig. 2(a) are significantly different from those of any other conventional TMR junctions. They exhibit the following unique $B$-dependent characteristics. (1) TMR ratio is tuned by the $B$ and can reach a signal about 20%. (2) The minimum of TMR ratio appears as $B$ approaches zero in $-B$ region. (3) The TMR ratios increase gradually crossing $B = 0$. (4) The peak of TMR ratio emerges in $+B$ region. A similar behavior is observed for polarity changes in $B$, i.e., when sweeping from $+B$ to $-B$ (the black line in Fig. 2).
observed in the Co/SiO₂/FGNPA junction is unique to the present TMR structure, and is driven by spin tunneling properties between the Co electrode and the FGNPA. Present reproducibility of the TMR behaviors is over 80%, because six of seven samples showed similar behaviors to date.

TMR properties observed at room temperature are shown in Fig. 2(b). Maximum TMR ratios decreases from ~20% to ~5% owing to the reduced flat-band ferromagnetism and the behaviors become much ambiguous compared with those at low temperatures, showing non-zero TMR ratios at high B due to thermal spin instability. It should be noticed that, nevertheless, TMR behaviors are still observable.

The observed unique TMR behavior can be qualitatively understood by considering the spin alignment between two opposing pore edges of the FGNPA (i.e., two edges of the interpore GNR region in Fig. 1(b)) and the Co electrode. It also clarifies spin ground states of the H-terminated zigzag-type GNRs under no B. We support these interpretations by atomistic simulations. First, we calculate the density of states (DOS) of a GNPA reminiscent of the fabricated structure. The calculated DOS (Fig. 2(c)) is compared to that obtained around 0.5 T, where half of the conductance channels are suppressed, resulting in the half value of conductance (Fig. 2(c)) and gradual increase in the TMR ratio (Fig. 2(d)) and subsequent the peak of TMR ratio observed around B = 0.5 T (Figs. 3(a) and 3(b)). These calculations suggest that gradual changes in TMR ratios can be actually possible. At higher +B, the spins of the Co injector start to align with the magnetic field, gradually quenching the TMR ratio, while non-zero TMR ratios in higher +B regions suggest instability of the pore edge spins of the FGNPAs as well as those in −B region.

It implies that the edge polarized spins of the interpore GNRs can actually tunnel through SiO₂ barrier forming the spin alignment with the spins of Co electrode and also that the spin ground states of the H-terminated zigzag-GNRs are AF under no B. This result is consistent with our previous experimental results, which exhibited ferromagnetism only when B is applied. This is important to note that the main mechanism revealed by our simulations does not depend on how the electrons are really injected from the cobalt electrode to the GNPA, but how efficiently spin-polarized electrons injected on the GNPA are further transmitted depending on the magnetic ordering of the local moments along the zigzag edges.

Here, we also demonstrate that the TMR characteristics can be controlled by changing a back gate voltage (Vbg; Fig. 1(d)) (Figs. 3(a) and 3(b)), as well as to the interpore spacing (W, i.e., width of interpore GNRs in Fig. 1(b)) (Figs. 3(c) and 3(d)). The TMR ratio exhibits a maximum value of ~20% at Vbg = +30 V (Figs. 3(a) and 3(b)), while it is reduced with decreasing Vbg toward −Vbg region. This is consistent with the presence of evident spin-based phenomena observed only at Vbg = +30 V for previous in-plane MR behaviors of FGNPAs. This is because the Au electrode was placed at the side position of the Co/SiO₂/FGNPA junction and the in-plane spin current path exists through the H-terminated FGNPA between the TMR junction and the Au electrode in the present specified sample structure (Fig. 1(d)). Although the polarized spins at the pore edges and TMR ratio themselves have basically no correlation with the Vbg, the spin current through the in-plane path is significantly reduced with decreasing Vbg due to the n-type semiconducting behavior of the interpore GNR regions of the GNPA. This makes TMR features difficult to detect, resulting in the decreases in the observed TMR ratios.

For larger interpore spacing of W ~ 40 nm, the TMR value further decreases significantly (Figs. 3(c) and 3(d)).
For such a large spacing, the spin polarization of opposing edge planes (i.e., two edges of interpore GNRs) becomes unstable due to suppressed spin interaction,\textsuperscript{13} quenching the TMR properties. TMR ratios also decrease when using FGNPAs with smaller $W$ (Figs. 3(c) and 3(d)), because $W \leq 20$ nm is too narrow to form spin currents along the in-plane current path through the FGNPA to Au electrode (Fig. 1(d)). Although ferromagnetism is stronger for smaller $W$,\textsuperscript{13} induced scattering by the nanopore array heavily obstructs spin flow to the Au electrode, reducing the TMR ratio. This is again consistent with previously observed spin-based phenomena in FGNPAs with $W \sim 30$ nm.\textsuperscript{13} Therefore, the optimum $W$ value exists for the TMR ratios.

We have presented unique TMR behaviors in the Co/SiO$_2$/FGNPA junctions. Nevertheless, the maximum TMR ratio is as low as $\sim 20\%$ at best (Fig. 2(a)). One of the main reasons is the poor interaction at the lattice-mismatched SiO$_2$/FGNPA interface, particularly at the H-terminated pore edges, which destructs transport of the spin-alignment current and reduces TMR ratios. In contrast, as shown in Fig. 4(a), we find that annealing of the SiO$_2$/FGNPA structure at $\sim 500$°C right after the deposition of SiO$_2$ tunneling layer drastically (i.e., $\approx 5$ times) improves the TMR ratios of Fig. 2(a), although some instability of the pore edge spins still remain as some irregular small TMR ratio peaks. At room temperature, the maximum TMR ratio increases even by $\sim 10$ times (Fig. 4(b)) compared to that in Fig. 2(b).

This promises that introducing a lattice-matched tunnel barrier layer (e.g., graphene oxide) instead of SiO$_2$ layer and also improvement of magnitude of the ferromagnetism in the FGNPAs (e.g., utilizing HSQ resist treatment\textsuperscript{13}) can increase TMR ratios further and make evident room-temperature operation possible. Moreover, realization of FGNPAs (lattice-matched tunnel barrier)/FGNPA junction must significantly improve the performance of the TMR behaviors toward $\sim 1000\%$ order.

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